

Docket No.: M4065.0123/P123-B
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Sukesh Sandhu et al.

(Continuation of 09/976,000
Filed: October 15, 2001)

Application No.: New

Prior Group Art Unit: 2822

Filed: July 10, 2003

Prior Examiner: K. Rose

For: HIGH COUPLING SPLIT-GATE
TRANSISTOR AND METHOD FOR ITS
FORMATION

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Prior to examination, please amend the above-captioned application as follows:

Amendments to the Title begin on page 2 of this paper.

Amendments to the Specification begin on page 3 of this paper.

Amendments to the Claims begin on page 4 of this paper.

Remarks begin on page 5 of this paper.

Application No. New

Docket No. M4065.0123/P123-B

Amendments to the Title:

Please replace the Title of the Invention with the following:

**HIGH COUPLING SPLIT-GATE TRANSISTOR ~~AND METHOD FOR ITS~~
FORMATION.**